

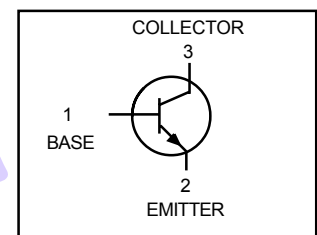


General Purpose Transistors

NPN Silicon

FEATURE

- High current capacity in compact package.
 $I_C = 1.5A$.
- Epitaxial planar type.
- NPN complement: 8050H
- We declare that the material of product compliance with RoHS requirements.
Pb-Free package is available
RoHS product for packing code suffix "G"
Halogen free product for packing code suffix "H"



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
8050HPLT1	1HA	3000/Tape&Reel
8050HQLT1	1HC	3000/Tape&Reel
8050HRLT1	1HE	3000/Tape&Reel
8050HSLT1	1HG	3000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	25	V
Collector-Base Voltage	V_{CBO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current-continuous	I_C	1500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	225 1.8	mW mW/ $^\circ C$
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Total Device Dissipation Alumina Substrate,(2) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	300 2.4	mW mW/ $^\circ C$
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	417	$^\circ C/W$
Junction and Storage Temperature	T_j, T_{stg}	-55 to +150	$^\circ C$



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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (I _C =1.0mA)	V _{(BR)CEO}	25	-	-	V
Emitter-Base Breakdown Voltage (I _E =100μA)	V _{(BR)EBO}	5	-	-	V
Collector-Base Breakdown Voltage (I _C =100μA)	V _{(BR)CBO}	40	-	-	V
Collector Cutoff Current (V _{CB} =35V)	I _{CBO}	-	-	150	nA
Emitter Cutoff Current (V _{EB} =4V)	I _{EBO}	-	-	150	nA

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

DC Current Gain I _C =100mA, V _{CE} =1V	h _{FE}	100	-	600	
Collector-Emitter Saturation Voltage (I _C =800mA I _B =80mA)	V _{CE(S)}	-	-	0.5	V

NOTE :

*	P	Q	R	S
h _{FE}	100~200	150~300	200~400	300~600



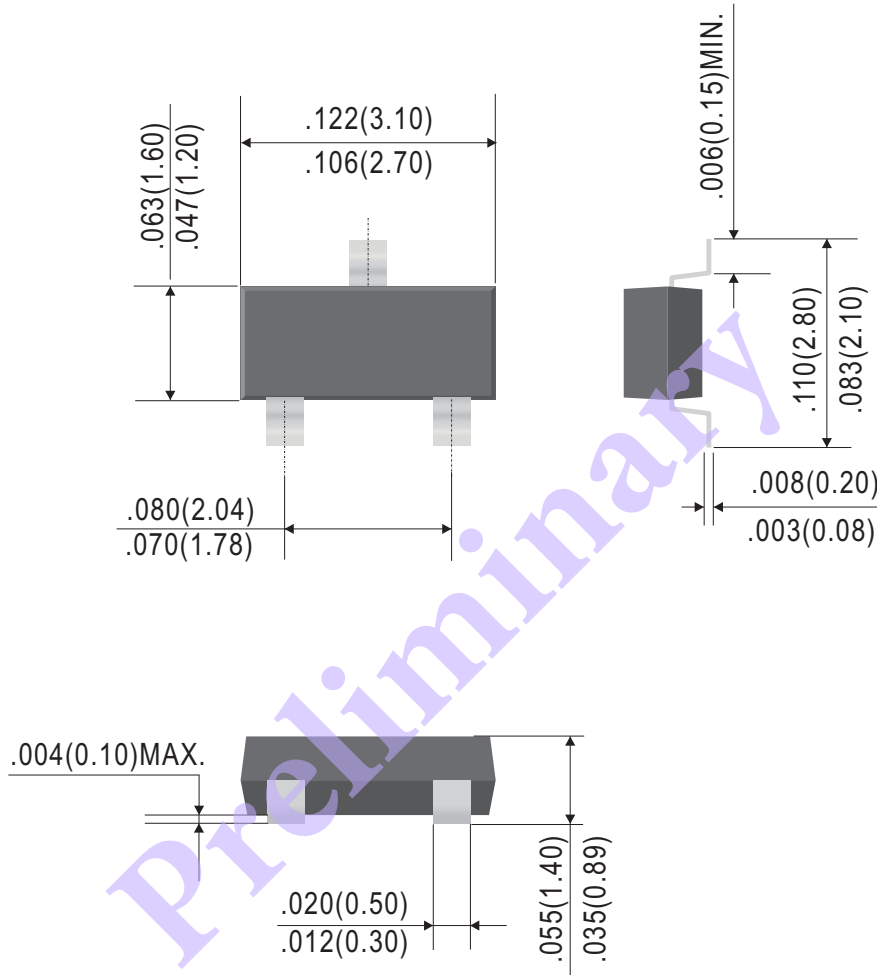
WILLAS



General Purpose Transistors

8050HxLT1

SOT-23



Dimensions in inches and (millimeters)

